

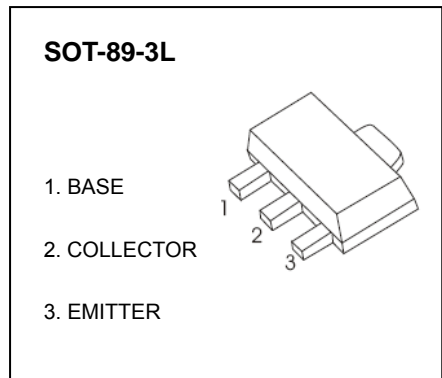
# TRANSISTOR(PNP)

## FEATURES

- Switching and Linear Amplification
- High Current and Low Voltage
- Complement to PXT2222A

**MARKING:p2F**

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**



Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-600	mA
P <sub>C</sub>	Collector Power Dissipation	500	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	250	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-60			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-50V, I <sub>E</sub> =0			-0.01	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.01	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-0.1mA	75			
		V <sub>CE</sub> =-10V, I <sub>C</sub> =-1mA	100			
		V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA	100			
		V <sub>CE</sub> =-10V, I <sub>C</sub> =-150mA	100		300	
		V <sub>CE</sub> =-10V, I <sub>C</sub> =-500mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-1.6	V
		I <sub>C</sub> =-150mA, I <sub>B</sub> =-15mA			-0.4	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-2.6	V
		I <sub>C</sub> =-150mA, I <sub>B</sub> =-15mA			-1.3	V
Delay time	t <sub>d</sub>	V <sub>CC</sub> =-30V, I <sub>C</sub> =-150mA, I <sub>B1</sub> =- I <sub>B2</sub> =-15mA			12	ns
Rise time	t <sub>r</sub>				30	ns
Storage time	t <sub>s</sub>				300	ns
Fall time	t <sub>f</sub>				65	ns
Transition frequency	f <sub>T</sub>		V <sub>CE</sub> =-10V, I <sub>C</sub> =-20mA, f=100MHz	200		